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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))	Docket No. FIS920040005US1

In Re Application Of: **Jochen Beintner, et al.**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/709,963	June 9, 2004	Unassigned	23389	2812	3962

Title: **RAISED STI PROCESS FOR MULTIPLE GATE OX AND SIDEWALL PROTECTION ON STRAINED Si/SGOI STRUCTURE WITH ELEVATED SOURCE/DRAIN**

Address to:
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P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

   ☐ the statement specified in 37 CFR 1.97(e);

   OR

   ☐ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

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FIS920040005US1

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Payment of Fee
(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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Leslie S. Szivos, Ph.D. Reg. No. 39,394

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Dated: **January 27, 2005**

cc:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):	Jochen Beintner, et al.	**Examiner:**	Unassigned
Serial No:	10/709,963	**Art Unit:**	2812
Filed:	June 9, 2004	**Docket:**	FIS920040005US1 (17369)
Dated:	January 27, 2005		
For:	RAISED STI PROCESS FOR MULTIPLE GATE OX AND SIDEWALL PROTECTION ON STRAINED Si/SGOI STRUCTURE WITH ELEVATED SOURCE/DRAIN		

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, applicants submit the following references which applicants believe may be material to the above-identified patent application. A copy of the references which applicants wish to make of record in this case is enclosed herein for the Examiner's convenience along with a listing on Form PTO-1449 attached.

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria, VA 22313-1450 on the date set forth below.

Dated: January 27, 2005

Leslie S. Szivos, Ph.D.

1. U.S. Patent No. 3,602,841, dated August 31, 1971, issued to McGroddy;

2. U.S. Patent No. 4,665,415, dated May 12, 1987, issued to Esaki, et al.;

3. U.S. Patent No. 4,853,076, dated August 1, 1989, issued to Tsaur, et al.;

4. U.S. Patent No. 4,855,245, dated August 8, 1989, issued to Neppl, et al.;

5. U.S. Patent No. 4,952,524, dated August 28, 1990, issued to Lee, et al.;

6. U.S. Patent No. 4,958,213, dated September 18, 1990, issued to Eklund, et al.;

7. U.S. Patent No. 5,006,913, dated April 9, 1991, issued to Sugahara, et al.;

8. U.S. Patent No. 5,060,030, dated October 22, 1991, issued to Hoke;

9. U.S. Patent No. 5,081,513, dated January 14, 1992, issued to Jackson, et al.;

10. U.S. Patent No. 5,108,843, dated April 28, 1992, issued to Ohtaka, et al.;

11. U.S. Patent No. 5,134,085, dated July 28, 1992, issued to Gilgen, et al.;

12. U.S. Patent No. 5,310,446, dated May 10, 1994, issued to Konishi, et al.;

13. U.S. Patent No. 5,354,695, dated October 11, 1994, issued to Leedy;

14. U.S. Patent No. 5,371,399, dated December 6, 1994, issued to Burroughes, et al.;

15. U.S. Patent No. 5,391,510, dated February 21, 1995, issued to Hsu, et al.;

16. U.S. Patent No. 5,459,346, dated October 17, 1995, issued to Asakawa, et al.;

17. U.S. Patent No. 5,471,948, dated December 5, 1995, issued to Burroughes, et al.;

18. U.S. Patent No. 5,557,122, dated September 17, 1996, issued to Shrivastava, et al.;

19. U.S. Patent No. 5,561,302, dated October 1, 1996, issued to Candelaria;

20. U.S. Patent No. 5,565,697, dated October 15, 1996, issued to Asakawa, et al.;

21. U.S. Patent No. 5,571,741, dated November 5, 1996, issued to Leedy, et al.;

22. U.S. Patent No. 5,592,007, dated January 7, 1997, issued to Leedy;

23. U.S. Patent No. 5,592,018, dated January 7, 1997, issued to Leedy;

24. U.S. Patent No. 5,670,798, dated September 23, 1997, issued to Schetzina;

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26. U.S. Patent No. 5,683,934, dated November 4, 1997, issued to Candelaria;

27. U.S. Patent No. 5,840,593, dated November 24, 1998, issued to Leedy;

28. U.S. Patent No. 5,861,651, dated January 19, 1999, issued to Brasen, et al.;

29. U.S. Patent No. 5,880,040, dated March 9, 1999, issued to Sun, et al.;

30. U.S. Patent No. 5,940,736, dated August 17, 1999, issued to Brady, et al.;

31. U.S. Patent No. 5,946,559, dated August 31, 1999, issued to Leedy;

32. U.S. Patent No. 5,960,297, dated September 28, 1999, issued to Saki;

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36. U.S. Patent No. 6,046,464, dated April 4, 2000, issued to Schetzina;

37. U.S. Patent No. 6,066,545, dated May 23, 2000; issued to Doshi, et al.;

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39. U.S. Patent No. 6,107,143, dated August 22, 2000, issued to Park, et al.;

40. U.S. Patent No. 6,117,722, dated September 12, 2000, issued to Wuu, et al.;

41. U.S. Patent No. 6,133,071, dated October 17, 2000, issued to Nagai;

42. U.S. Patent No. 6,165,383, dated December 26, 2000, issued to Chou;

43. U.S. Patent No. 6,221,735, dated April 24, 2001, issued to Manley, et al.;

44. U.S. Patent No. 6,228,694, dated May 8, 2001, issued to Doyle, et al.;

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46. U.S. Patent No. 6,255,169, dated July 3, 2001, issued to Li, et al.;

47. U.S. Patent No. 6,261,964, dated July 17, 2001, issued to Wu, et al.;

48. U.S. Patent No. 6,265,317, dated July 24, 2001, issued to Chiu, et al.;

49. U.S. Patent No. 6,274,444, dated August 14, 2001, issued to Wang;

50. U.S. Patent No. 6,281,532, dated August 28, 2001, issued to Doyle, et al.;

51. U.S. Patent No. 6,284,623, dated September 4, 2001, issued to Zhang, et al.;

52. U.S. Patent No. 6,284,626, dated September 4, 2001, issued to Kim;

53. U.S. Patent No. 6,319,794, dated November 20, 2001, issued to Akatsu, et al.;

54. U.S. Patent No. 6,361,885, dated March 26, 2002, issued to Chou;

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56. U.S. Patent No. 6,368,931, dated April 9, 2002, issued to Kuhn, et al.;

57. U.S. Patent No. 6,403,486, dated June 11, 2002, issued to Lou;

58. U.S. Patent No. 6,403,975, dated June 11, 2002, issued to Brunner, et al.;

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61. U.S. Patent No. 6,476,462, dated November 5, 2002, issued to Shimizu, et al.;

62. U.S. Patent No. 6,493,497, dated December 10, 2002, issued to Ramdani, et al.;

63. U.S. Patent No. 6,498,358, dated December 24, 2002, issued to Lach, et al.;

64. U.S. Patent No. 6,501,121, dated December 31, 2002, issued to Yu, et al.;

65. U.S. Patent No. 6,506,652, dated January 14, 2003, issued to Jan, et al.;

66. U.S. Patent No. 6,509,618, dated January 21, 2003, issued to Jan, et al.;

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68. U.S. Patent No. 6,531,369, dated March 11, 2003, issued to Ozkan, et al.;

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70. U.S. Patent Application Publication No. 2001/0009784 A1, dated July 26, 2001, issued to Ma, et al.;

71. U.S. Patent Application Publication No. 2002/0074598 A1, dated June 20, 2002, issued to Doyle, et al.;

72. U.S. Patent Application Publication No. 2002/0086472 A1, dated July 4, 2002, issued to Roberds, et al.;

73. U.S. Patent Application Publication No. 2002/0086497 A1, dated July 4, 2002, issued to Kwok;

74. U.S. Patent Application Publication No. 2002/0090791 A1, dated July 11, 2002, issued to Doyle, et al.;

75. U.S. Patent Application Publication No. 2003/0032261 A1, dated February 13, 2003, issued to Yeh, et al.;

76. U.S. Patent Application Publication No. 2003/0040158 A1, dated February 27, 2003, issued to Saitoh;

77. U.S. Patent Application Publication No. 2003/0057184 A1, dated March 27, 2003, issued to Yu, et al.;

78. U.S. Patent Application Publication No. 2003/0067035 A1, dated April 10, 2003, issued to Tews, et al.; and

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80. Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si *n*-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998;

81. Rim, et al. "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99;

82. Scott, et al. "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999;

83. Ootsuka, et al. "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Device Meeting, 23.5.1, IEEE, April 2000;

84. Ito, et al. "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000;

85. Shimizu, et al. "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001;

86. Ota, et al. "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

87. Ouyang, et al. "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFETS With Enhanced Device Performance and Scalability", Microelectronics Research Center, pp 151-154, 2000 IEEE.

88. Sayama et al., "Effect of <Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15um Gate Length"ULSI Development Center, pp27.5.1-27.5.4, 1999 IEEE.

89. European Patent Application Publication No. EPO 01/62362, 26/06/89, issued to Hasegawa, Michihiko;

90. European Patent Application Publication No. EP 1 174 928 A1, dated 01/23/02, issued to Hitachi Ltd.;

91. European Patent Application Publication No. EP 0 967 636 A2, dated 12/29/1999, issued to Rengarajan, et al.;

92. International Patent Application Publication No. WO 02/454156 A2, dated 06/06/2002, issued to Armstrong et al.;

93. International Application Publication No. WO 94/27317, dated 05/06/1993, issued to Winnerl, et al.;

Applicant is submitting copies of the above-cited non-U.S. Patent references. Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

In accordance with the waiver of 37 C.F.R. § 1.98 (a)(2)(i), per 1276 OG 55, August 5, 2003, applicants are not required to submit copies of the above-cited U.S. Patent references.

Respectfully submitted,

Leslie S. Szivos
Registration No. 39,394

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PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO.
FIS920040005US1 (17369)	10/709,963
APPLICANTS	
Jochen Beintner, et al.	
FILING DATE	GROUP ART UNIT
June 9, 2004	2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		3,602,841	08/31/71	McGroddy			
		4,665,415	05/12/87	Esaki, et al			
		4,853,076	08/01/89	Tsaur, et al			
		4,855,245	08/08/89	Neppl, et al			
		4,952,524	08/28/90	Lee, et al			
		4,958,213	09/18/90	Eklund, et al			
		5,006,913	04/09/91	Sugahara, et al			
		5,060,030	10/22/91	Hoke			
		5,081,513	01/14/92	Jackson, et al			
		5,108,843	04/28/92	Ohtaka, et al			
		5,134,085	07/28/92	Gilgen, et al			
		5,310,446	05/10/94	Konishi, et al			
		5,354,695	10/11/94	Leedy			
		5,371,399	12/6/94	Burroughes, et al			
		5,391,510	02/21/95	Hsu, et al			
		5,459,346	10/17/95	Asakawa, et al			
		5,471,948	12/05/95	Burroughes, et al			
		5,557,122	09/17/96	Shrivastava, et al			
		5,561,302	10/01/96	Candelaria			
		5,565,697	10/15/96	Asakawa, et al			
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		5,592,018	01/07/97	Leedy			
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		5,679,965	10/21/97	Schetzina			
		5,683,934	11/04/97	Candelaria			
		5,840,593	11/24/98	Leedy			
		5,861,651	01/19/99	Brasen, et al			
		5,880,040	03/09/99	Sun, et al			

Examiner | Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		6,025,280	02/15/00	Brady, et al			
		6,046,464	04/04/00	Schetzina			
		6,066,545	05/23/00	Doshi, et al			
		6,090,684	07/18/00	Ishitsuka, et al			
		6,107,143	08/22/00	Park, et al			
		6,117,722	09/12/00	Wuu, et al			
		6,133,071	10/17/00	Nagai			
		6,165,383	12/26/00	Chou			
		6,221,735	04/24/01	Manley, et al			
		6,228,694	05/08/01	Doyle, et al			
		6,246,095	06/12/01	Brady, et al			
		6,255,169	07/03/01	Li, et al			
		6,261,964	07/17/01	Wu, et al			
		6,265,317	07/24/01	Chiu, et al			
		6,274,444	08/14/01	Wang			
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		6,284,623	09/04/01	Zhang, et al			
		6,284,626	09/04/01	Kim			
		6,319,794	11/20/01	Akatsu, et al			
		6,361,885	03/26/02	Chou			
		6,362,082	03/26/02	Doyle, et al			
		6,368,931	04/09/02	Kuhn, et al			
		6,403,486	06/11/02	Lou			
		6,403,975	06/11/02	Brunner, et al			
		6,406,973	06/18/02	Lee			
		6,461,936	10/18/02	Von Ehrenwall			
		6,476,462	11/05/02	Shimizu, et al			

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		6,493,497	12/10/02	Ramdani, et al			
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		6,501,121	12/31/02	Yu, et al			
		6,506,652	01/14/03	Jan, et al			
		6,509,618	01/21/03	Jan, et al			
		6,521,964	02/18/03	Jan, et al			
		6,531,369	03/11/03	Ozkan, et al			
		6,531,740	03/11/03	Bosco, et al			

U.S. PATENT APPLICATION PUBLICATION DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2001/0009784 A1	07/26/01	Ma, et al			
		2002/0074598 A1	07/20/02	Doyle, et al			
		2002/0086472 A1	07/04/02	Roberds, et al			
		2002/0086497 A1	07/04/02	Kwok			
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		2003/0040158 A1	02/27/03	Saitoh			
		2003/0057184 A1	03/27/03	Yu, et al			
		2003/0067035 A1	04/10/03	Tews, et al			

Examiner	Date Considered

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LIST OF PRIOR ART CITED BY APPLICANT

(Use several sheets if necessary)

Atty. Docket No.	Serial No.
FIS920040005US1 (17369)	10/709,963
Applicants Jochen Beintner, et al.	
Filing Date June 9, 2004	**Group** 2812

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
		EPO 01/62362	26/06/89	Europe				
		EP 1 174 928 A1	01/23/02	Europe				
		EP 0 967 636 A2	12/29/1999	Europe				
		WO 02/454156 A2	06/06/2002	PCT				
		WO 94/27317	05/06/1993	PCT				

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

		Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si *n*-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998
		Rim, et al. "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99
		Scott, et al. "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999
		Ootsuka, et al. "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Device Meeting, 23.5.1, IEEE, April 2000
		Ito, et al. "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000
		Shimizu, et al. "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001
		Ota, et al. "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002
		Ouyang, et al. "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFETS With Enhanced Device Performance and Scalability", Microelectronics Research Center, pp 151-154, 2000 IEEE
		Sayama et al., "Effect of <Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15um Gate Length"ULSI Development Center, pp27.5.1-27.5.4, 1999 IEEE

EXAMINER	DATE CONSIDERED

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